

100V 10mohm N-channel SGT MOSFET
AKG100N10G

Description:

This N channel SGT MOSFET has been designed to low on-state resistance low switching loss with good E_{AS} performance, especially for DC-DC and Motor driving applications.

Features:

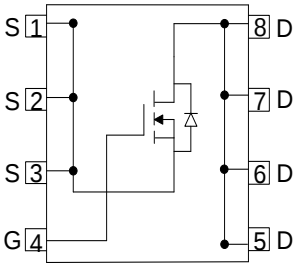
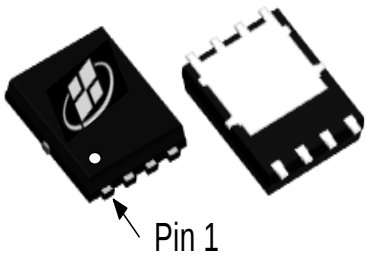
- Ultra-low on-resistance
- RoHS compliant ^(Note 1)
- Halogen-free ^(Note 1)

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on), max} @V_{GS} = 10V$	10	mΩ
I_D	55	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AKG100N10G	DFN5X6	G100N10G	Tape Reel	5000PCS

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	100	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) ^(Note 1)	55	A
	Drain Current - Continuous ($T_C = 100^\circ\text{C}$)	35	A
I_{DM}	Drain Current - Pulsed ^(Note 2)	220	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy ^(Note 3)	90	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	57	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Steady-State	2.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Steady State ^(Note 4)	50	$^\circ\text{C/W}$

Notes:

1. The max drain current rating is package limited
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $L = 0.5\text{ mH}$, $V_{DD} = 50\text{V}$, $I_{AS} = 19\text{ A}$, $R_G = 25\ \Omega$, Starting $T_J = 25\ ^\circ\text{C}$
4. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V,			1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V			±100	nA
V _{GS(TH)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.2	2	2.8	V
R _{DS(ON)}	Drain-Source on-state resistance	V _{GS} = 10 V, I _D = 20 A		8	10	mΩ
		V _{GS} = 4.5 V, I _D = 15 A		10.5	13.5	mΩ
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{DS} = 50 V, V _{GS} = 0 V, F = 1 MHz		2198		pF
C _{OSS}	Output Capacitance			508		pF
C _{RSS}	Reverse Transfer Capacitance			23		pF
R _G	Gate Resistance	F = 1 MHz		4.7		Ω
Switching Characteristics						
T _{D(ON)}	Turn On Delay Time	V _{DD} = 50 V , R _L = 2.5 Ω, V _{GS} = 10 V, R _G = 6 Ω		13		nS
T _R	Rise Time			38		nS
T _{D(OFF)}	Turn Off Delay Time			41		nS
T _F	Fall Time			52		nS
Q _G	Total Gate Charge	V _{DD} = 50 V , I _D = 20 A, V _{GS} = 10 V		35		nC
Q _{GS}	Gate-Source Charge			6		nC
Q _{GD}	Gate-Drain Charge			8		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Body-Diode Forward Current			55		A
I _{SM}	Maximum Pulsed Body-Diode Forward Current ^(NOTE 1)			220		A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 1 A		0.7	1	V
T _{RR}	Reverse recovery time	V _{DD} = 50 V, I _D = 15 A, di/dt = 100 A/μS		53		ns
Q _{RR}	Reverse recovery charge			75		nC
I _{RRM}	Peak Reverse Recovery Current			2.4		A

Electrical Characteristics Diagrams

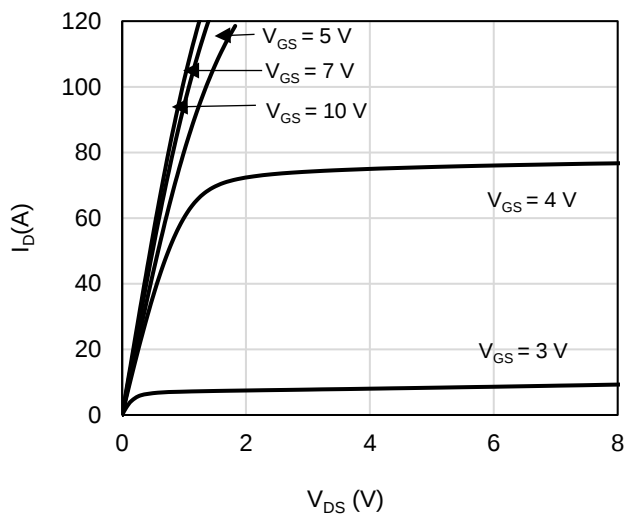


Figure 1: On-Region Characteristics

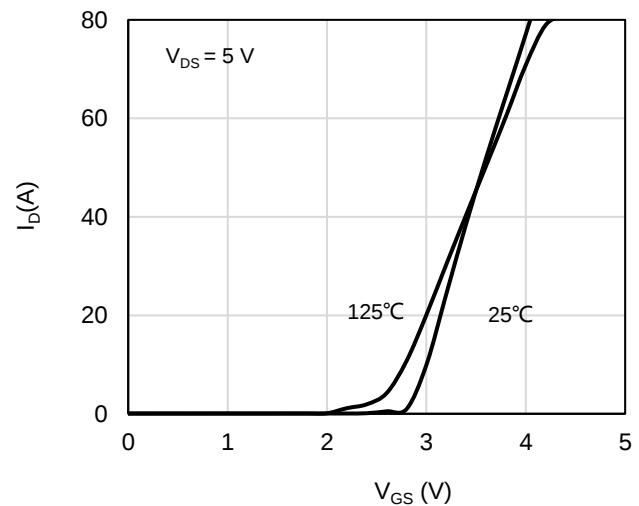


Figure 2: Transfer Characteristics

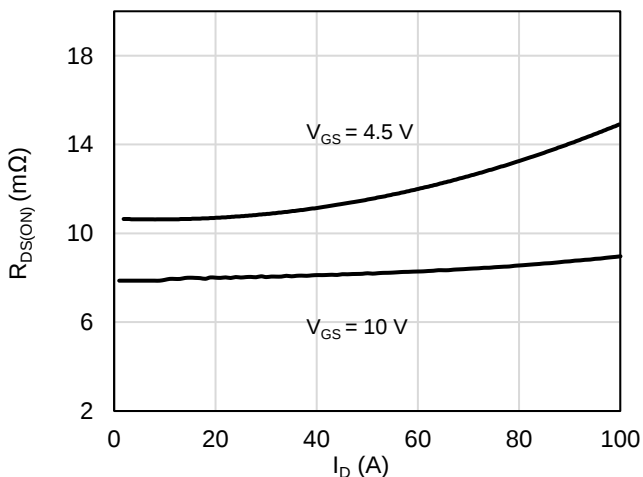


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

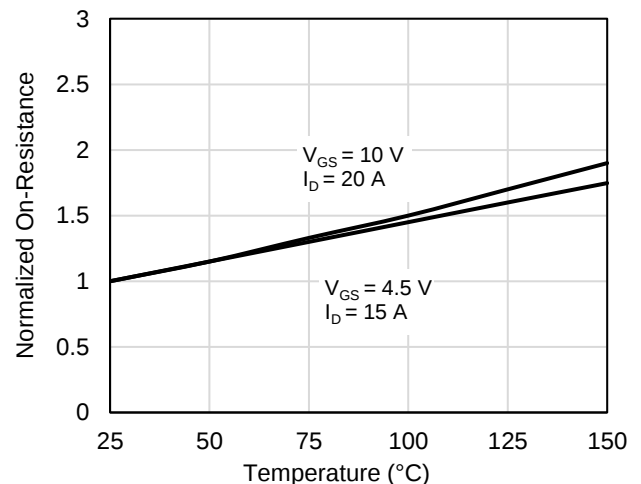


Figure 4: On-Resistance vs. Junction Temperature

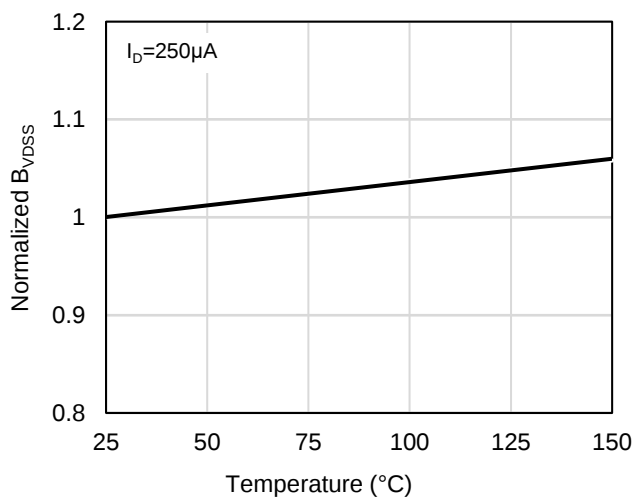


Figure 5: Breakdown Voltage vs. Junction Temperature

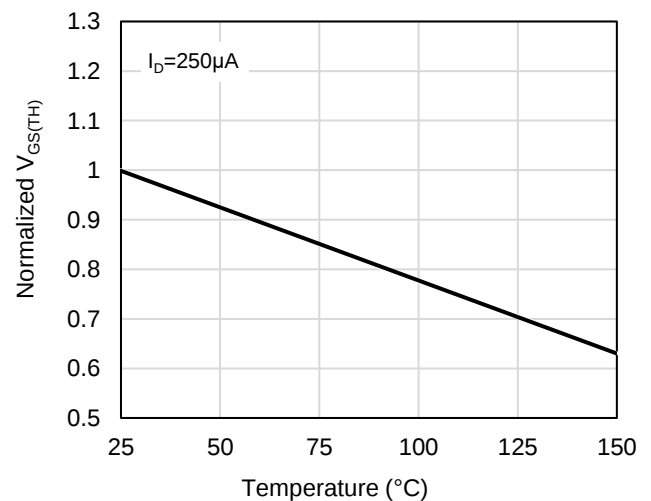
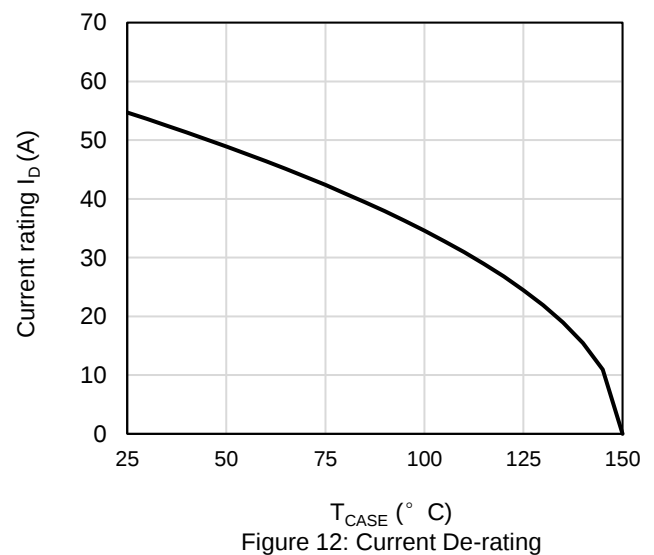
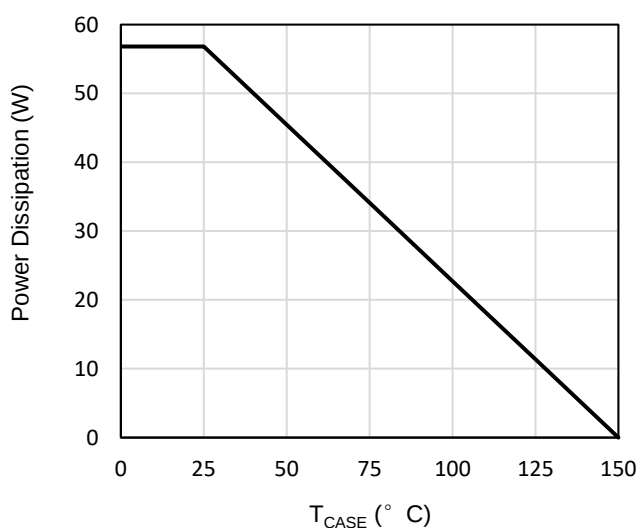
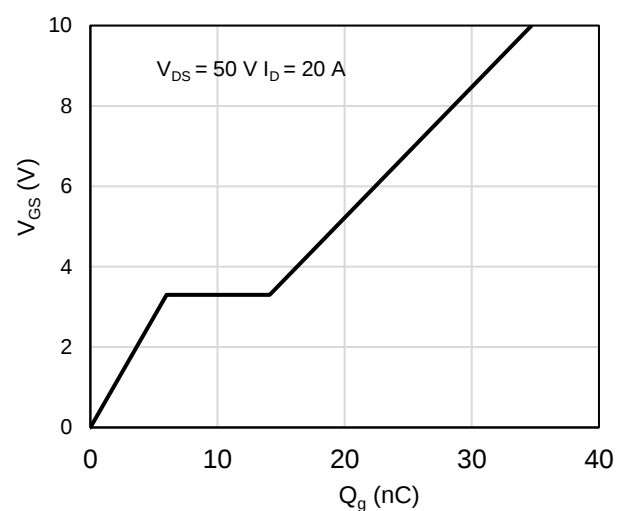
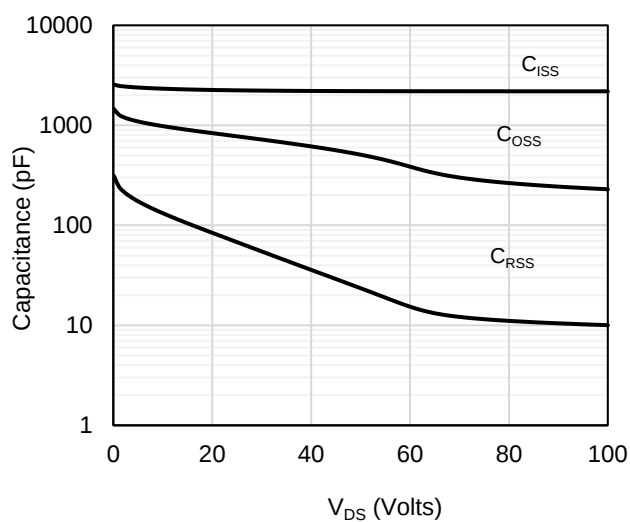
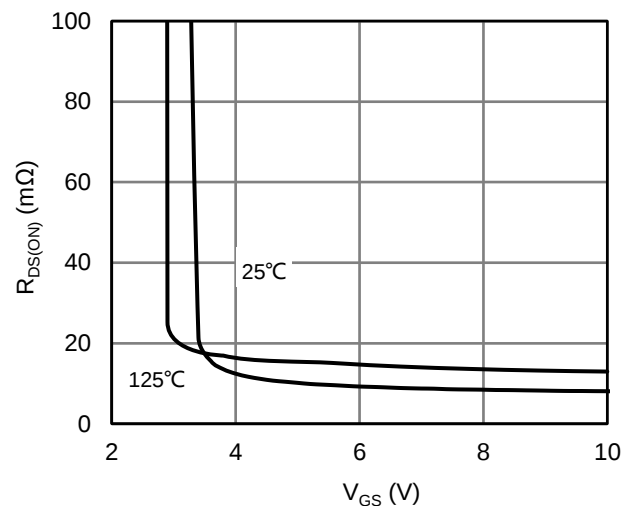
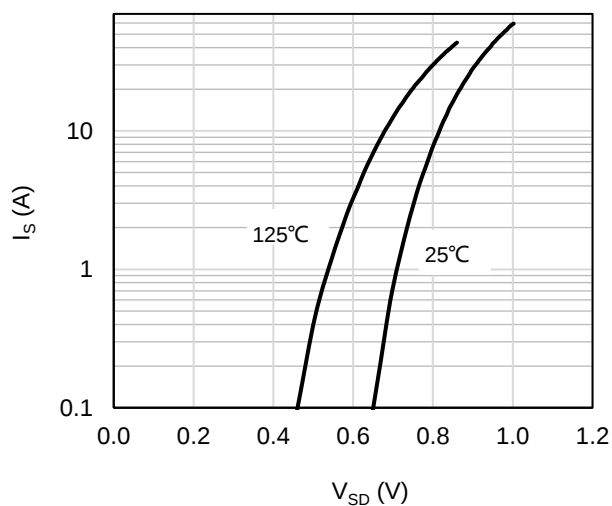
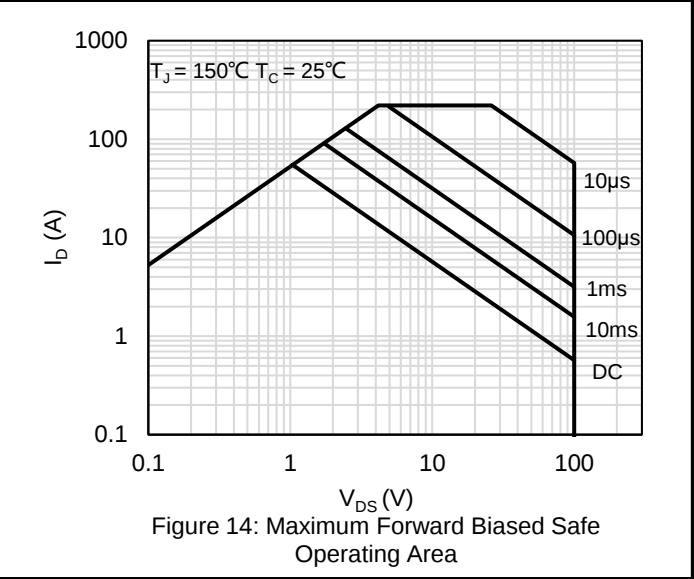
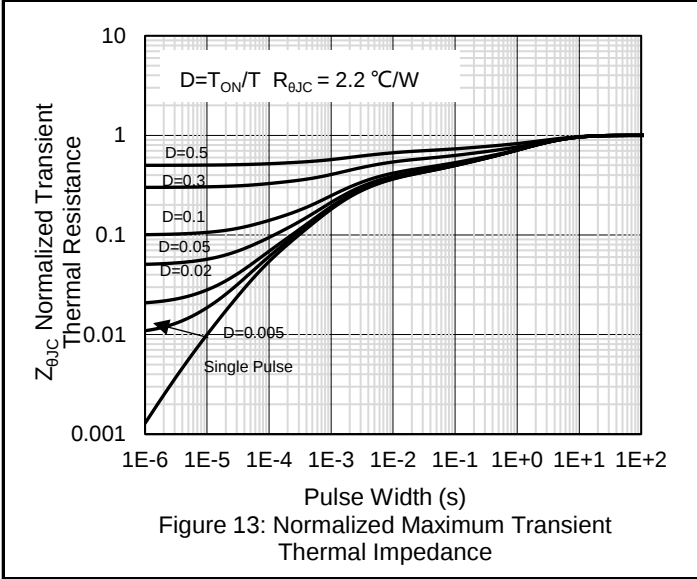


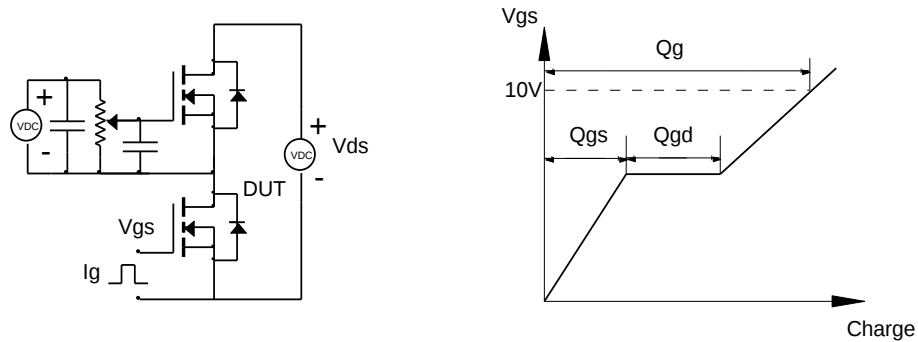
Figure 6: Threshold Voltage vs. Junction Temperature



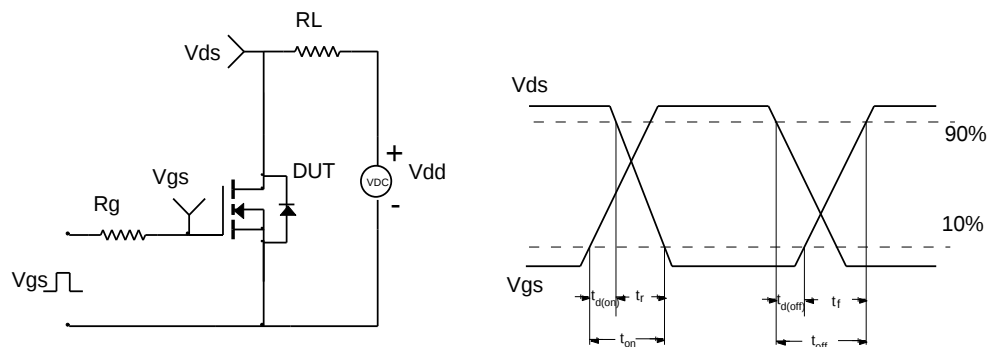


Test Circuit and Waveform

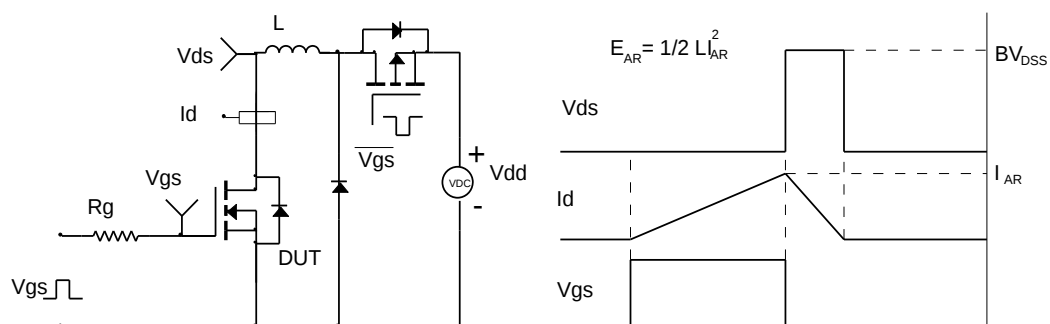
Gate Charge Test Circuit & Waveform



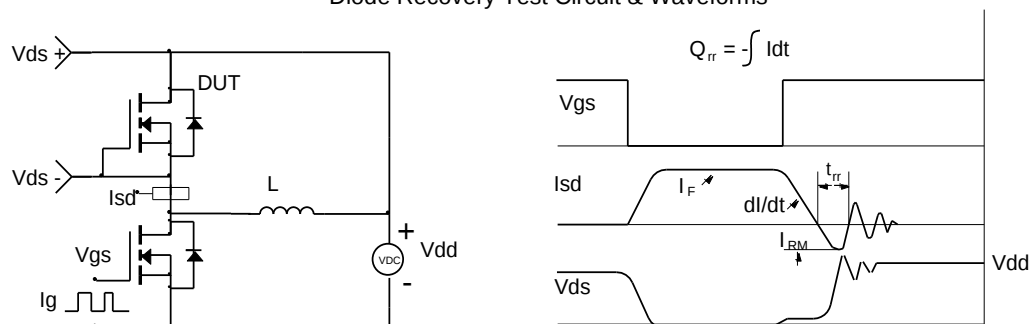
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



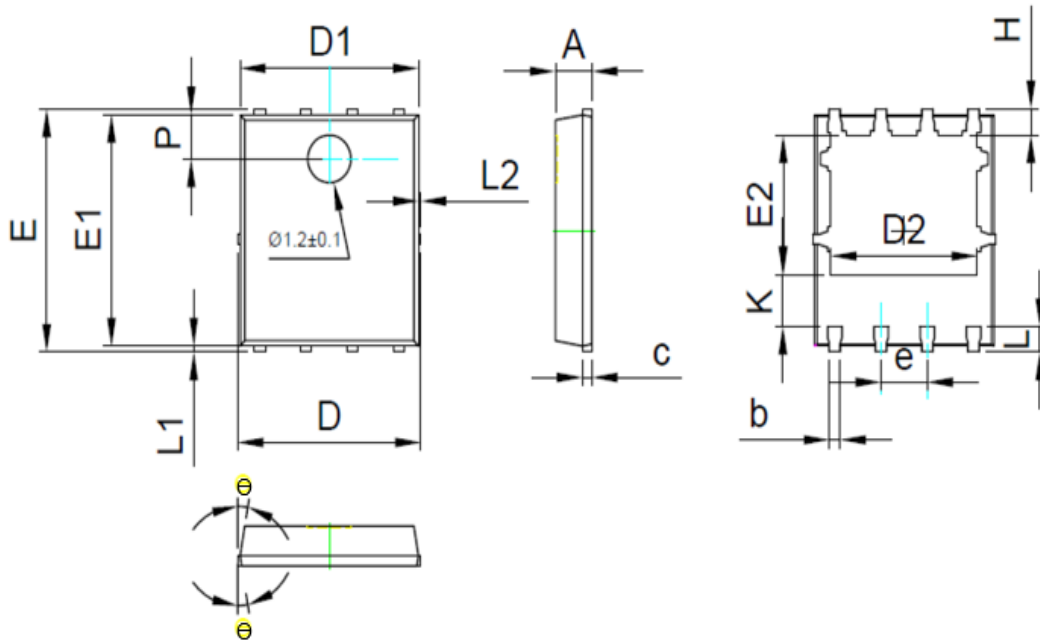
Diode Recovery Test Circuit & Waveforms



Package Outlines

Package Dimensions : PDFN 5*6 PACKAG

E



COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.35	0.40	0.45
c	0.21	0.25	0.34
D	-	-	5.1
D1	4.85	4.90	4.95
D2	3.96	4.01	4.06
e	1.27 BSC		
E	5.95	6.00	6.05
E1	5.70	5.75	5.80
E2	3.425	3.475	3.525
H	0.60	0.65	0.70
K	1.29	-	-
L	0.60	0.65	0.70
L1	0.05	0.15	0.25
L2	-	-	0.12
θ	8°	10°	12°
P	1.05	1.10	1.15

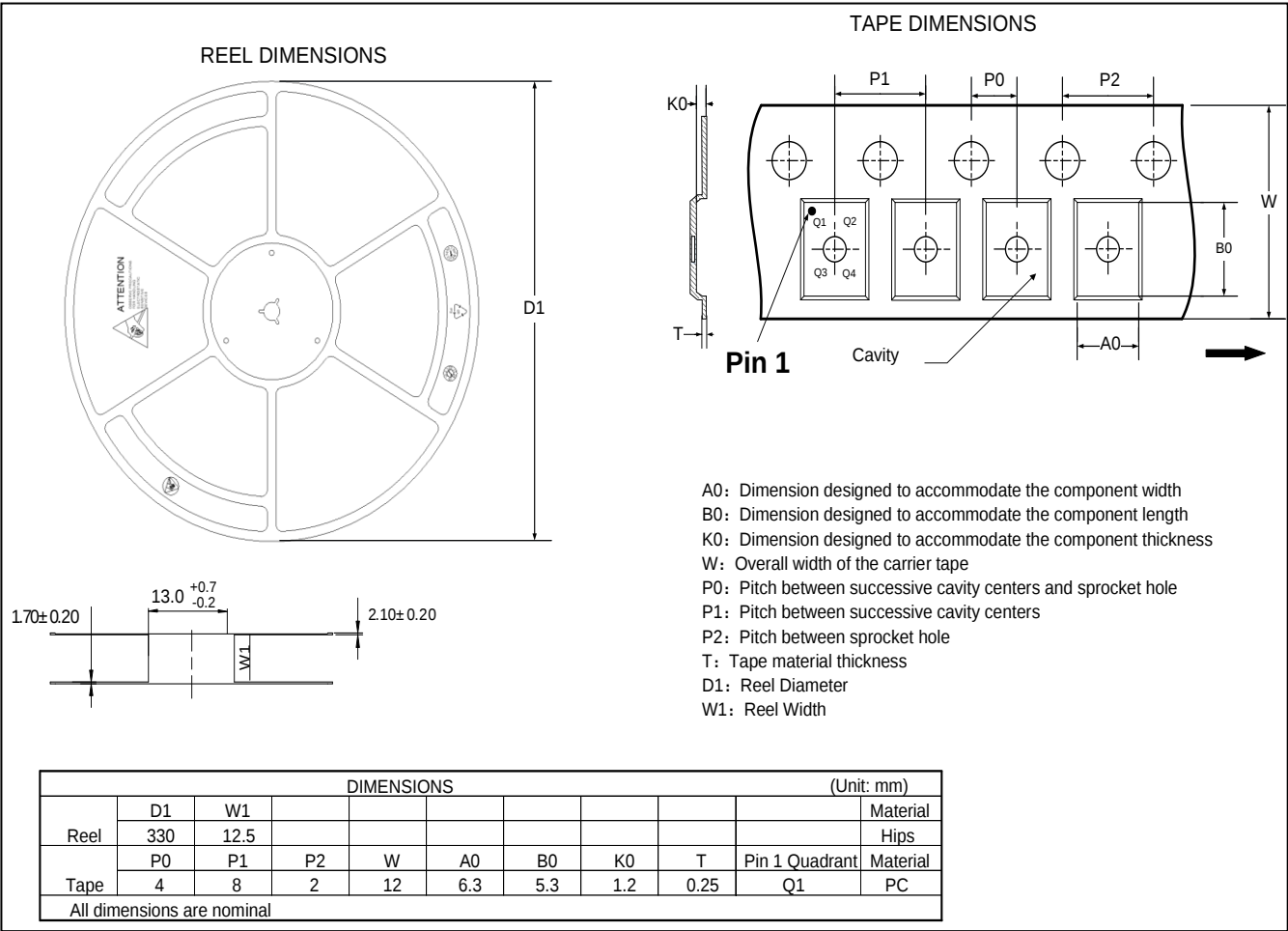


Marking Information



G100N10G
XXXX

Note:
G100N10G = Product Name Code
XXXX = Date code
Contact ALKAIDSEMI sales for detail information



Revision History

Revision	Release Date	Remark
Rev.1.0	2022/7/7	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.